TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

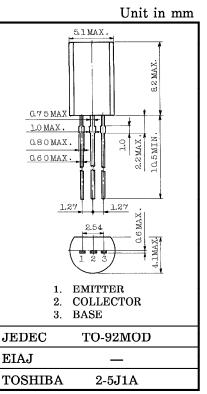
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DRIVER STAGE AUDIO AMPLIFIER APPLICATIONS. HIGH VOLTAGE SWITCHING APPLICATIONS.

- High Breakdown Voltage : $V_{CEO} = -150V$
- Low Output Capacitance $: C_{ob} = 5.0 pF (Max.)$
- High Transition Frequency : $f_T = 120 MHz$ (Typ.)

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	-150	V
Collector-Emitter Voltage	VCEO	-150	V
Emitter-Base Voltage	VEBO	-5	V
Collector Current	IC	-50	mA
Base Current	IB	5	mA
Collector Power Dissipation	PC	800	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	$-55 \sim 150$	°C



Weight : 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = -150V, I_E = 0$	_	_	-0.1	μA
Emitter Cut-off Current	I _{EBO}	$V_{EB} = -5V, I_C = 0$	_	_	-0.1	μA
DC Current Gain	h _{FE} (Note)	$V_{CE} = -5V, I_C = -10mA$	70	_	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = -10 \text{mA}, I_{B} = -1 \text{mA}$	_	_	-0.8	v
Base-Emitter Voltage	V _{BE}	$V_{CE} = -5V, I_C = -30mA$	_		-0.9	V
Transition Frequency	f_{T}	$V_{CE} = -30V, I_C = -10mA$	_	120	_	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	4.0	5.0	pF

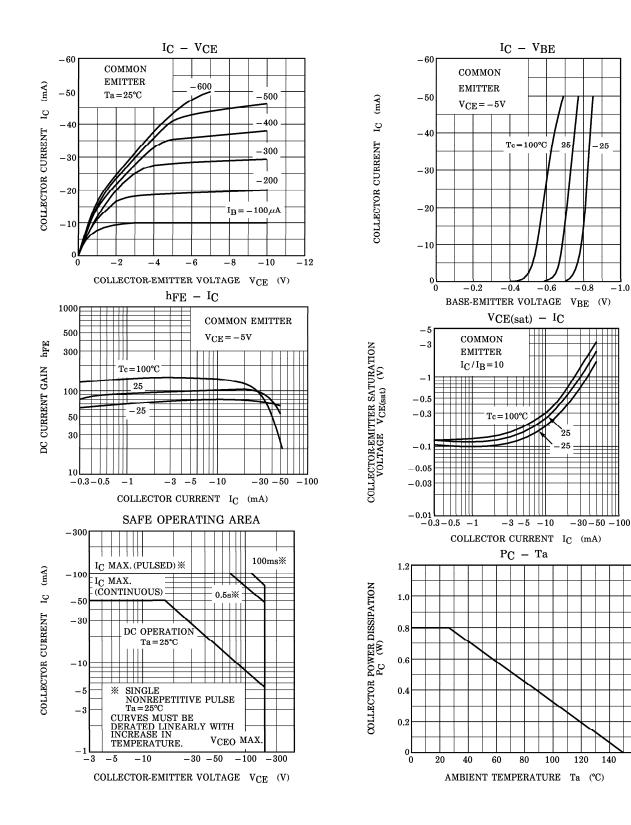
O:70~140, Y:120~240 Note : hFE Classification

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